# MUN5332DW1, NSBC143EPDXV6, NSBC143EPDP6

# Complementary Bias Resistor Transistors R1 = 4.7 kΩ, R2 = 4.7 kΩ

## NPN and PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

### Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable*
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

($T_A$ = 25°C both polarities $Q_1$ (PNP) & $Q_2$ (NPN), unless otherwise noted)

| Rating | Symbol | Max | Unit |
|---|---|---|---|
| Collector-Base Voltage | $V_{CBO}$ | 50 | Vdc |
| Collector-Emitter Voltage | $V_{CEO}$ | 50 | Vdc |
| Collector Current – Continuous | $I_C$ | 100 | mAdc |
| Input Forward Voltage | $V_{IN(fwd)}$ | 30 | Vdc |
| Input Reverse Voltage | $V_{IN(rev)}$ | 10 | Vdc |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### ORDERING INFORMATION

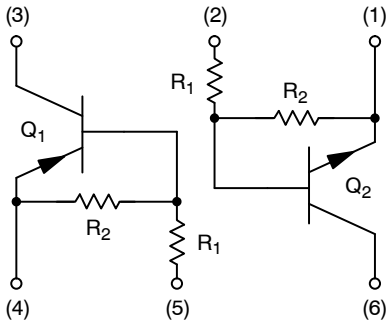
| Device | Package | Shipping† |
|---|---|---|
| MUN5332DW1T1G, NSVMUN5332DW1T1G* | SOT−363 | 3,000/Tape & Reel |
| NSVMUN5332DW1T3G* | SOT−363 | 10,000/Tape & Reel |
| NSBC143EPDXV6T1G | SOT−563 | 4,000/Tape & Reel |
| NSBC143EPDP6T5G | SOT−963 | 8,000/Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**ON Semiconductor®**

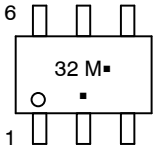
www.onsemi.com

### PIN CONNECTIONS

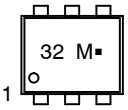



### MARKING DIAGRAMS

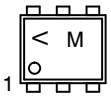
**SOT−363**
**CASE 419B**




**SOT−563**
**CASE 463A**




**SOT−963**
**CASE 527AD**




32/V = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

© Semiconductor Components Industries, LLC, 2013

## THERMAL CHARACTERISTICS

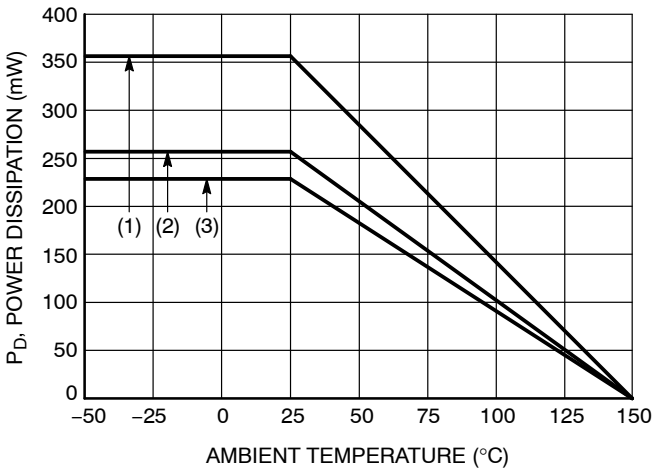
| Characteristic | Symbol | Max | Unit |
|---|---|---|---|
| **MUN5332DW1 (SOT−363) ONE JUNCTION HEATED** | | | |
| Total Device Dissipation<br>$T_A$ = 25°C (Note 1)<br>(Note 2)<br>Derate above 25°C (Note 1)<br>(Note 2) | $P_D$ | <br>187<br>256<br>1.5<br>2.0 | <br>mW<br><br>mW/°C |
| Thermal Resistance, (Note 1)<br>Junction to Ambient (Note 2) | $R_{\theta JA}$ | 670<br>490 | °C/W |
| **MUN5332DW1 (SOT−363) BOTH JUNCTION HEATED** (Note 3) | | | |
| Total Device Dissipation<br>$T_A$ = 25°C (Note 1)<br>(Note 2)<br>Derate above 25°C (Note 1)<br>(Note 2) | $P_D$ | <br>250<br>385<br>2.0<br>3.0 | <br>mW<br><br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient (Note 1)<br>(Note 2) | $R_{\theta JA}$ | <br>493<br>325 | °C/W |
| Thermal Resistance,<br>Junction to Lead (Note 1)<br>(Note 2) | $R_{\theta JL}$ | <br>188<br>208 | °C/W |
| Junction and Storage Temperature Range | $T_J$, $T_{stg}$ | −55 to +150 | °C |
| **NSBC143EPDXV6 (SOT−563) ONE JUNCTION HEATED** | | | |
| Total Device Dissipation<br>$T_A$ = 25°C (Note 1)<br>Derate above 25°C (Note 1) | $P_D$ | <br>357<br>2.9 | <br>mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient (Note 1) | $R_{\theta JA}$ | <br>350 | °C/W |
| **NSBC143EPDXV6 (SOT−563) BOTH JUNCTION HEATED** (Note 3) | | | |
| Total Device Dissipation<br>$T_A$ = 25°C (Note 1)<br>Derate above 25°C (Note 1) | $P_D$ | <br>500<br>4.0 | <br>mW<br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient (Note 1) | $R_{\theta JA}$ | <br>250 | °C/W |
| Junction and Storage Temperature Range | $T_J$, $T_{stg}$ | −55 to +150 | °C |
| **NSBC143EPDP6 (SOT−963) ONE JUNCTION HEATED** | | | |
| Total Device Dissipation<br>$T_A$ = 25°C (Note 4)<br>(Note 5)<br>Derate above 25°C (Note 4)<br>(Note 5) | $P_D$ | <br>231<br>269<br>1.9<br>2.2 | <br>MW<br><br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient (Note 4)<br>(Note 5) | $R_{\theta JA}$ | <br>540<br>464 | °C/W |
| **NSBC143EPDP6 (SOT−963) BOTH JUNCTION HEATED** (Note 3) | | | |
| Total Device Dissipation<br>$T_A$ = 25°C (Note 4)<br>(Note 5)<br>Derate above 25°C (Note 4)<br>(Note 5) | $P_D$ | <br>339<br>408<br>2.7<br>3.3 | <br>MW<br><br>mW/°C |
| Thermal Resistance,<br>Junction to Ambient (Note 4)<br>(Note 5) | $R_{\theta JA}$ | <br>369<br>306 | °C/W |
| Junction and Storage Temperature Range | $T_J$, $T_{stg}$ | −55 to +150 | °C |

1. FR−4 @ Minimum Pad.
2. FR−4 @ 1.0 × 1.0 Inch Pad.
3. Both junction heated values assume total power is sum of two equally powered channels.
4. FR−4 @ 100 $mm^2$, 1 oz. copper traces, still air.
5. FR−4 @ 500 $mm^2$, 1 oz. copper traces, still air.

**ELECTRICAL CHARACTERISTICS** ($T_A$ = 25°C both polarities $Q_1$ (PNP) & $Q_2$ (NPN), unless otherwise noted)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | |
| Collector-Base Cutoff Current ($V_{CB}$ = 50 V, $I_E$ = 0) | $I_{CBO}$ | – | – | 100 | nAdc |
| Collector-Emitter Cutoff Current ($V_{CE}$ = 50 V, $I_B$ = 0) | $I_{CEO}$ | – | – | 500 | nAdc |
| Emitter-Base Cutoff Current ($V_{EB}$ = 6.0 V, $I_C$ = 0) | $I_{EBO}$ | – | – | 1.5 | mAdc |
| Collector-Base Breakdown Voltage ($I_C$ = 10 μA, $I_E$ = 0) | $V_{(BR)CBO}$ | 50 | – | – | Vdc |
| Collector-Emitter Breakdown Voltage (Note 6) ($I_C$ = 2.0 mA, $I_B$ = 0) | $V_{(BR)CEO}$ | 50 | – | – | Vdc |
| **ON CHARACTERISTICS** | | | | | |
| DC Current Gain (Note 6) ($I_C$ = 5.0 mA, $V_{CE}$ = 10 V) | $h_{FE}$ | 15 | 30 | – | |
| Collector-Emitter Saturation Voltage (Note 6) ($I_C$ = 10 mA, $I_B$ = 1.0 mA) | $V_{CE(sat)}$ | – | – | 0.25 | V |
| Input Voltage (Off) ($V_{CE}$ = 5.0 V, $I_C$ = 100 μA) (NPN) ($V_{CE}$ = 5.0 V, $I_C$ = 100 μA) (PNP) | $V_{i(off)}$ | –<br>– | 1.2<br>1.2 | –<br>– | Vdc |
| Input Voltage (On) ($V_{CE}$ = 0.2 V, $I_C$ = 20 mA) (NPN) ($V_{CE}$ = 0.2 V, $I_C$ = 20 mA) (PNP) | $V_{i(on)}$ | –<br>– | 2.4<br>2.8 | –<br>– | Vdc |
| Output Voltage (On) ($V_{CC}$ = 5.0 V, $V_B$ = 2.5 V, $R_L$ = 1.0 kΩ) | $V_{OL}$ | – | – | 0.2 | Vdc |
| Output Voltage (Off) ($V_{CC}$ = 5.0 V, $V_B$ = 0.25 V, $R_L$ = 1.0 kΩ) | $V_{OH}$ | 4.9 | – | – | Vdc |
| Input Resistor | R1 | 3.3 | 4.7 | 6.1 | kΩ |
| Resistor Ratio | $R_1/R_2$ | 0.8 | 1.0 | 1.2 | |

6. Pulsed Condition: Pulse Width = 300 ms, Duty Cycle ≤ 2%.




(1) SOT−363; 1.0 × 1.0 Inch Pad
(2) SOT−563; Minimum Pad
(3) SOT−963; 100 $mm^2$, 1 oz. Copper Trace

**Figure 1. Derating Curve**

## TYPICAL CHARACTERISTICS – NPN TRANSISTOR
## MUN5332DW1, NSBC143EPDXV6

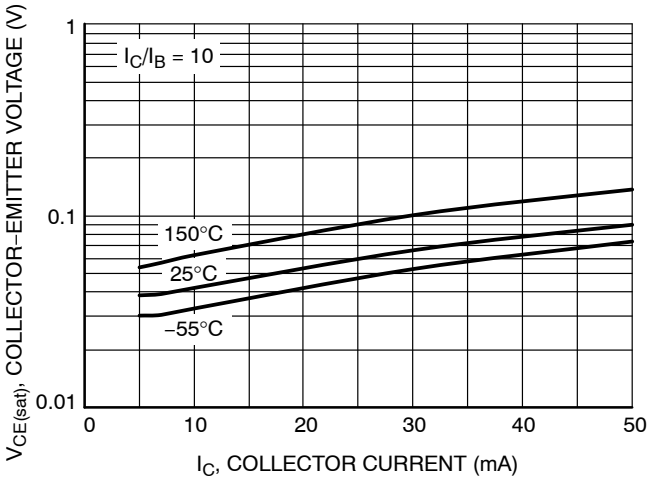



**Figure 2. $V_{CE(sat)}$, vs. $I_C$**

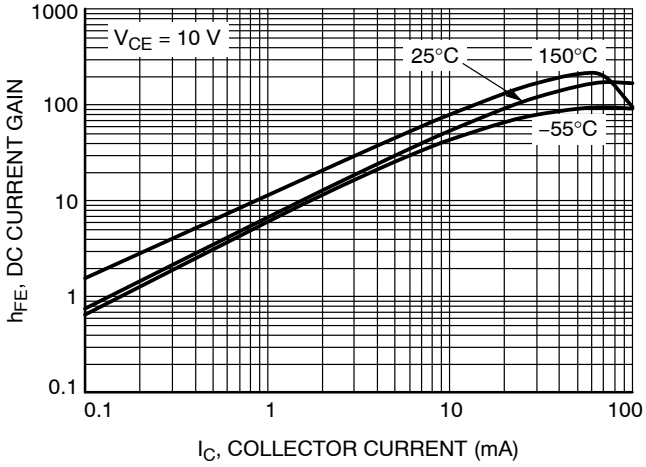



**Figure 3. DC Current Gain**

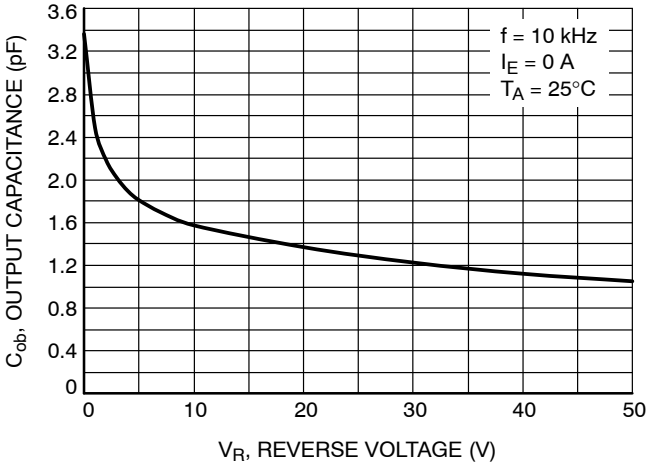



**Figure 4. Output Capacitance**

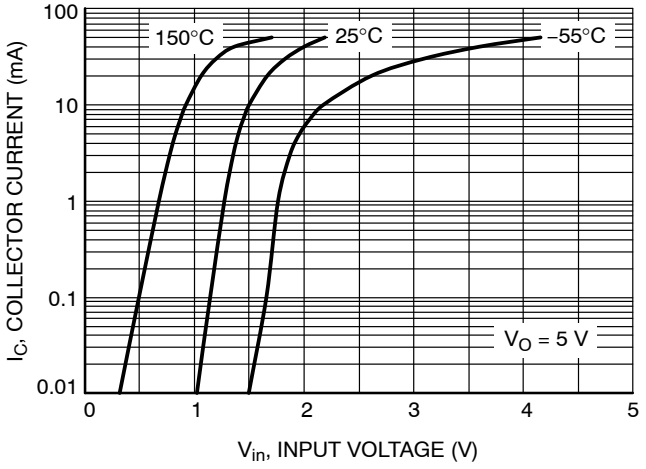



**Figure 5. Output Current vs. Input Voltage**

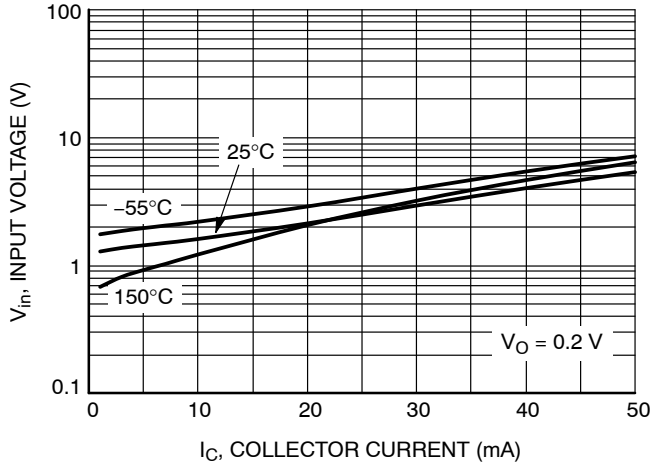



**Figure 6. Input Voltage vs. Output Current**

## TYPICAL CHARACTERISTICS – PNP TRANSISTOR
## MUN5332DW1, NSBC143EPDXV6

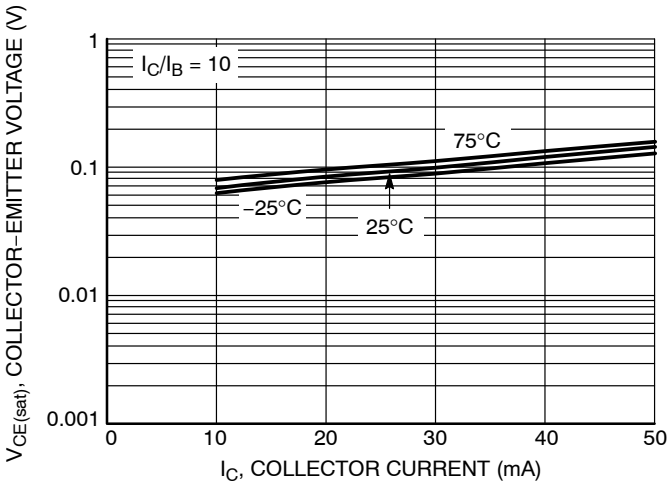



**Figure 7. $V_{CE(sat)}$ vs. $I_C$**

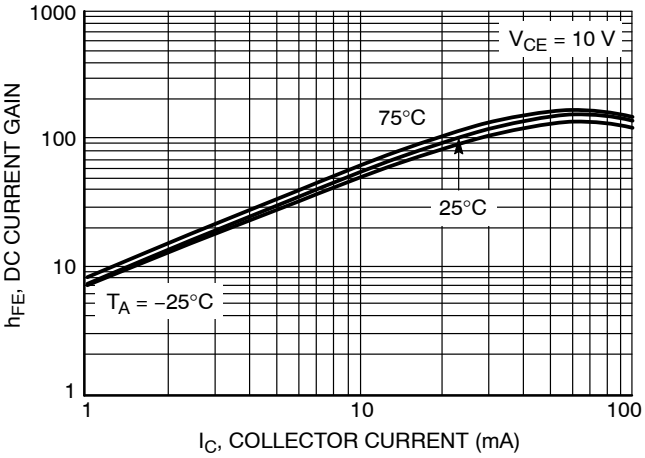



**Figure 8. DC Current Gain**

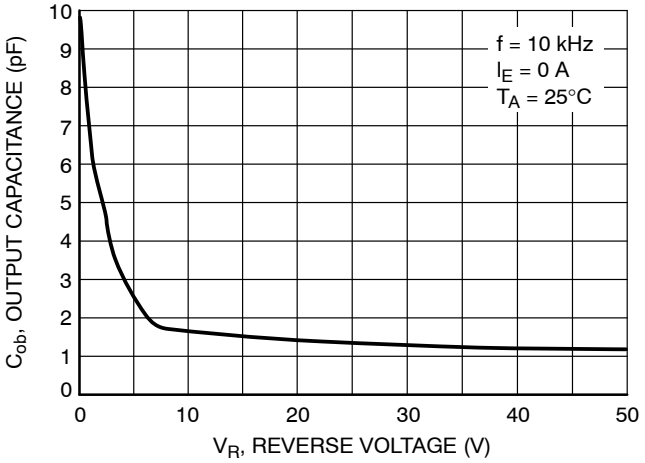



**Figure 9. Output Capacitance**

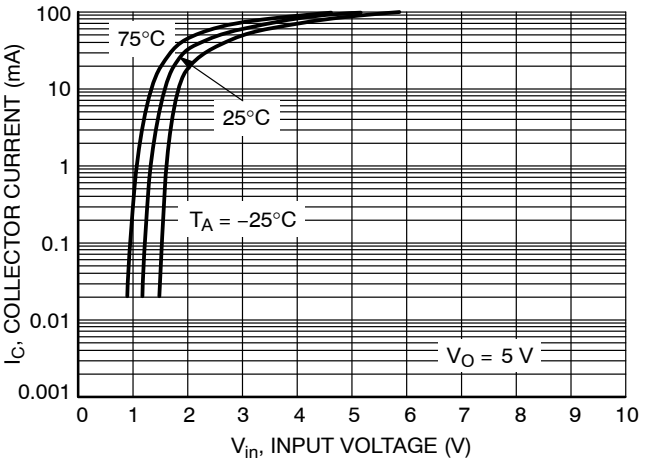



**Figure 10. Output Current vs. Input Voltage**

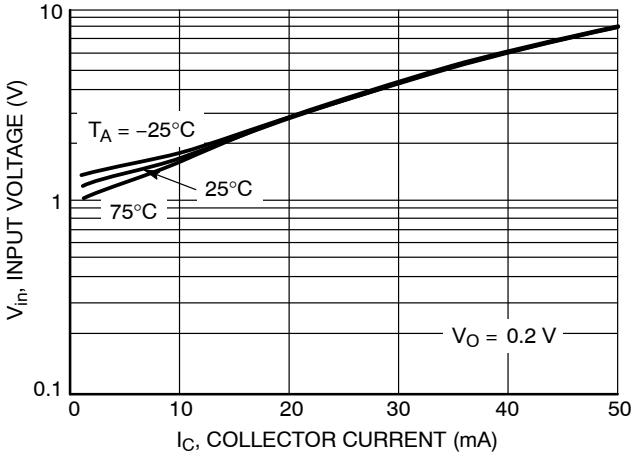



**Figure 11. Input Voltage vs. Output Current**

## TYPICAL CHARACTERISTICS – NPN TRANSISTOR
## NSBC143EPDP6

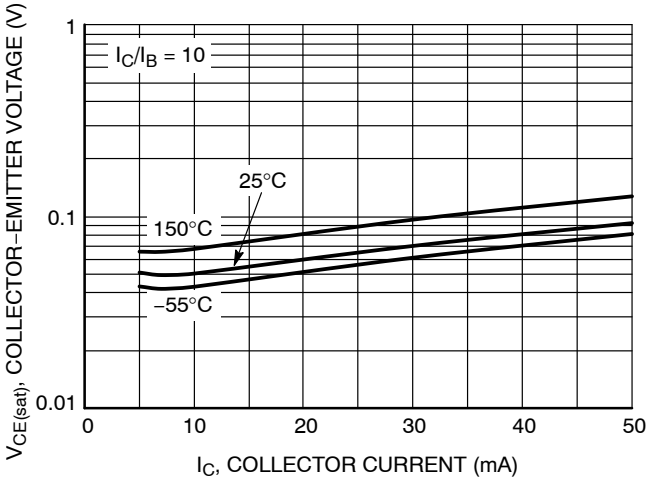



**Figure 12. $V_{CE(sat)}$, vs. $I_C$**

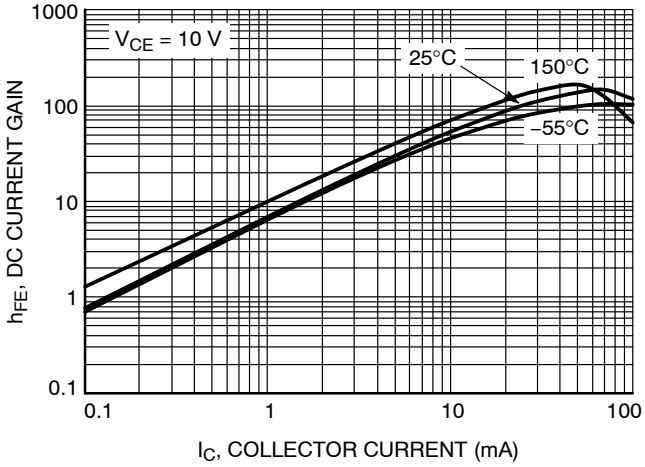



**Figure 13. DC Current Gain**

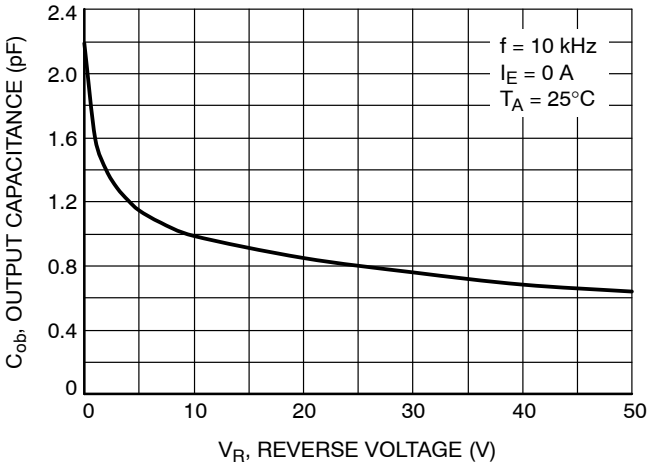



**Figure 14. Output Capacitance**

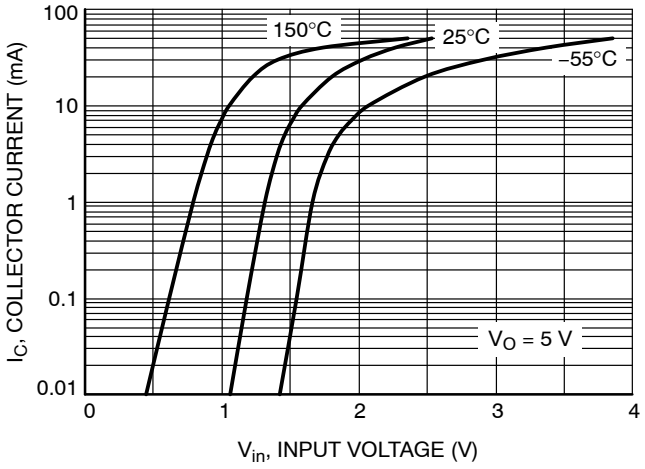



**Figure 15. Output Current vs. Input Voltage**

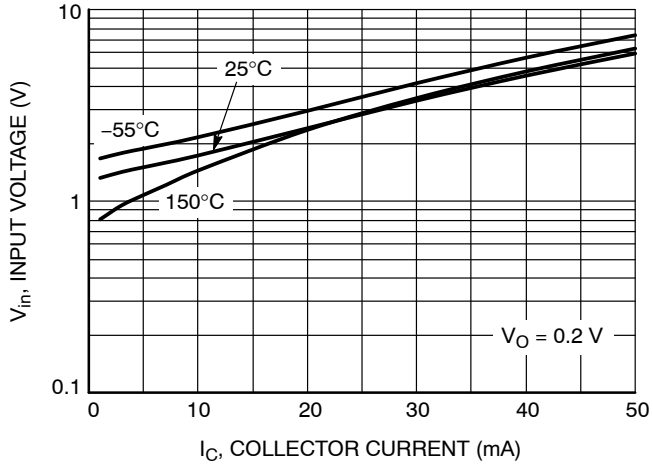



**Figure 16. Input Voltage vs. Output Current**

## TYPICAL CHARACTERISTICS – PNP TRANSISTOR NSBC143EPDP6

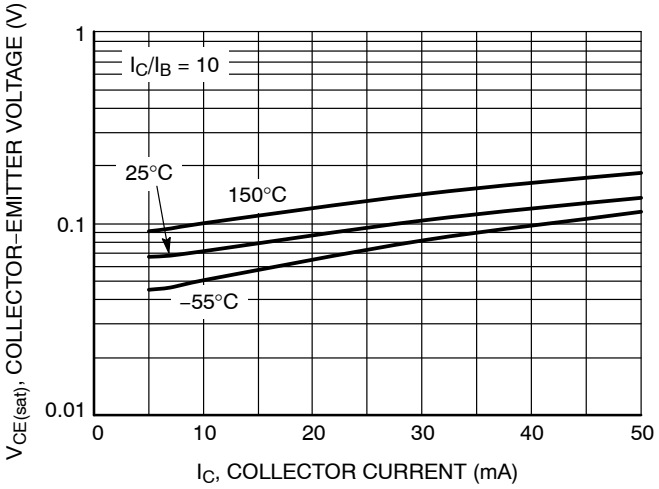



**Figure 17. $V_{CE(sat)}$ vs. $I_C$**

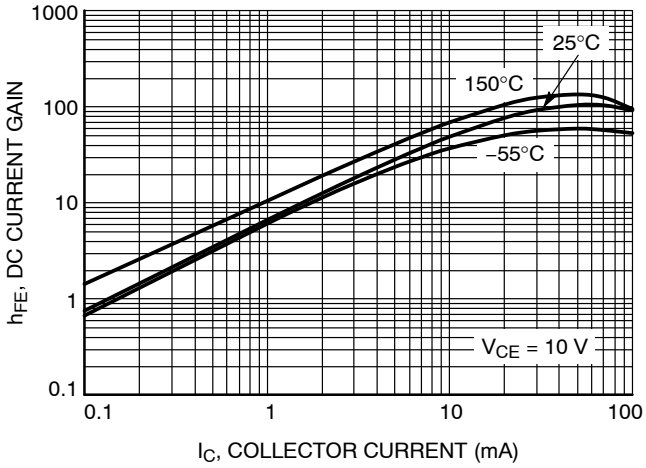



**Figure 18. DC Current Gain**

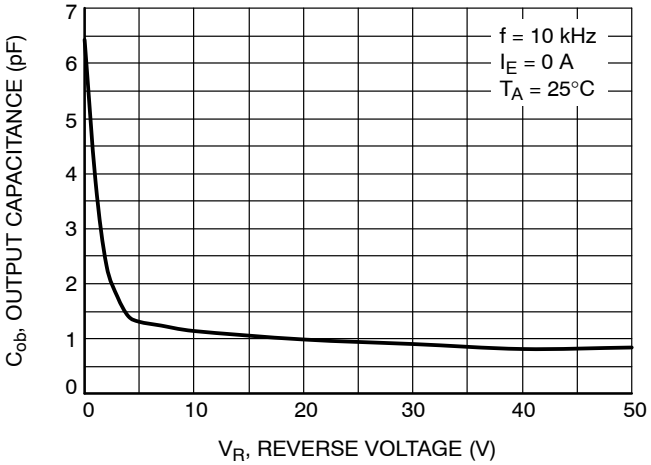



**Figure 19. Output Capacitance**

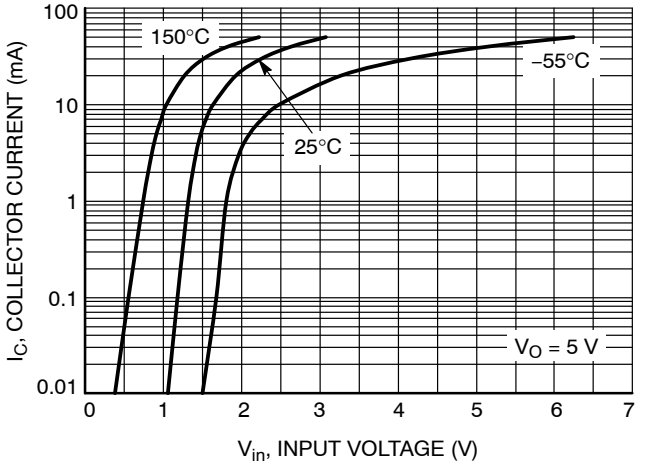



**Figure 20. Output Current vs. Input Voltage**

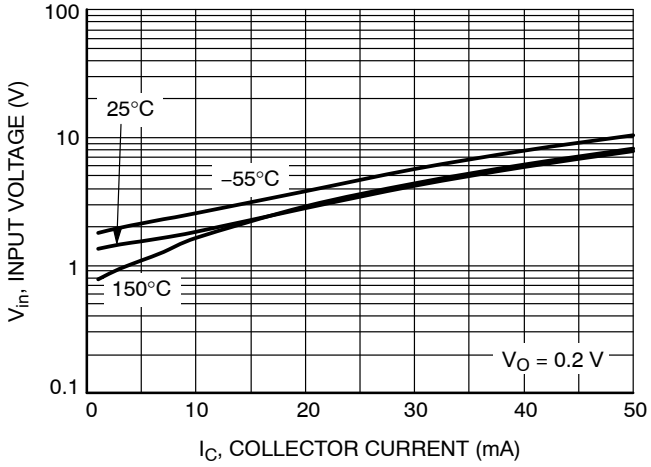
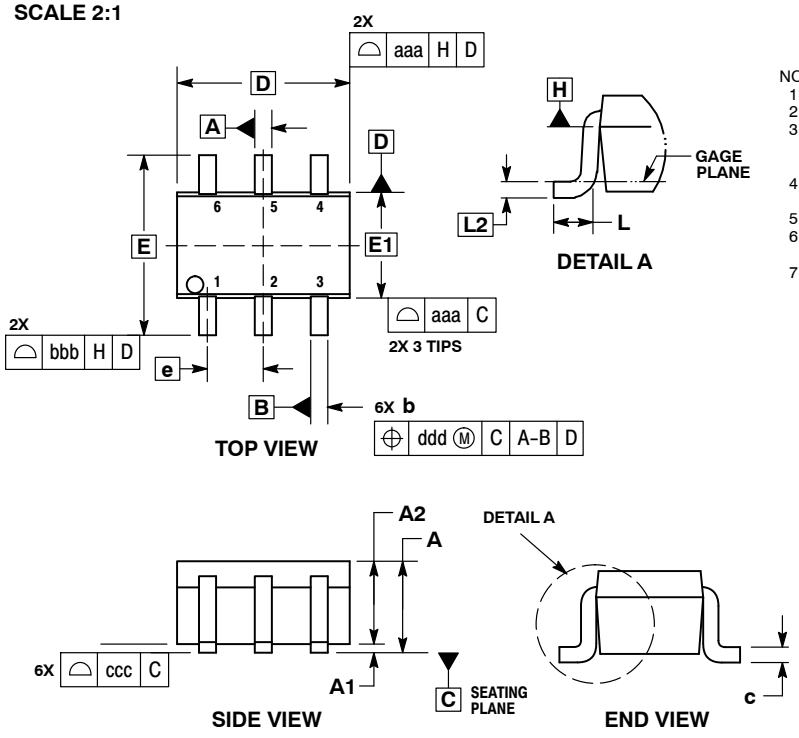



**Figure 21. Input Voltage vs. Output Current**

**SC−88/SC70−6/SOT−363**
CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

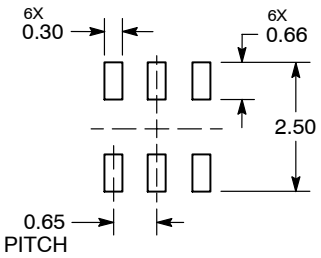
1
**SCALE 2:1**




NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
5. DATUMS A AND B ARE DETERMINED AT DATUM H.
6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

| | MILLIMETERS | | | INCHES | | |
|---|---|---|---|---|---|---|
| **DIM** | **MIN** | **NOM** | **MAX** | **MIN** | **NOM** | **MAX** |
| **A** | −−− | −−− | 1.10 | −−− | −−− | 0.043 |
| **A1** | 0.00 | −−− | 0.10 | 0.000 | −−− | 0.004 |
| **A2** | 0.70 | 0.90 | 1.00 | 0.027 | 0.035 | 0.039 |
| **b** | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 |
| **C** | 0.08 | 0.15 | 0.22 | 0.003 | 0.006 | 0.009 |
| **D** | 1.80 | 2.00 | 2.20 | 0.070 | 0.078 | 0.086 |
| **E** | 2.00 | 2.10 | 2.20 | 0.078 | 0.082 | 0.086 |
| **E1** | 1.15 | 1.25 | 1.35 | 0.045 | 0.049 | 0.053 |
| **e** | 0.65 BSC | | | 0.026 BSC | | |
| **L** | 0.26 | 0.36 | 0.46 | 0.010 | 0.014 | 0.018 |
| **L2** | 0.15 BSC | | | 0.006 BSC | | |
| **aaa** | 0.15 | | | 0.006 | | |
| **bbb** | 0.30 | | | 0.012 | | |
| **ccc** | 0.10 | | | 0.004 | | |
| **ddd** | 0.10 | | | 0.004 | | |

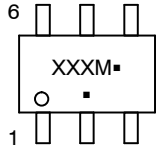
### RECOMMENDED SOLDERING FOOTPRINT*




DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### GENERIC MARKING DIAGRAM*




XXX = Specific Device Code
M = Date Code*
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "▪", may or may not be present. Some products may not follow the Generic Marking.


**STYLES ON PAGE 2**





**onsemi** and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2019

**SC−88/SC70−6/SOT−363**
CASE 419B−02
ISSUE Y

DATE 11 DEC 2012

STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

STYLE 2:
CANCELLED

STYLE 3:
CANCELLED

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. COLLECTOR
4. EMITTER
5. BASE
6. ANODE

STYLE 5:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 6:
PIN 1. ANODE 2
2. N/C
3. CATHODE 1
4. ANODE 1
5. N/C
6. CATHODE 2

STYLE 7:
PIN 1. SOURCE 2
2. DRAIN 2
3. GATE 1
4. SOURCE 1
5. DRAIN 1
6. GATE 2

STYLE 8:
CANCELLED

STYLE 9:
PIN 1. EMITTER 2
2. EMITTER 1
3. COLLECTOR 1
4. BASE 1
5. BASE 2
6. COLLECTOR 2

STYLE 10:
PIN 1. SOURCE 2
2. SOURCE 1
3. GATE 1
4. DRAIN 1
5. DRAIN 2
6. GATE 2

STYLE 11:
PIN 1. CATHODE 2
2. CATHODE 2
3. ANODE 1
4. CATHODE 1
5. CATHODE 1
6. ANODE 2

STYLE 12:
PIN 1. ANODE 2
2. ANODE 2
3. CATHODE 1
4. ANODE 1
5. ANODE 1
6. CATHODE 2

STYLE 13:
PIN 1. ANODE
2. N/C
3. COLLECTOR
4. EMITTER
5. BASE
6. CATHODE

STYLE 14:
PIN 1. VREF
2. GND
3. GND
4. IOUT
5. VEN
6. VCC

STYLE 15:
PIN 1. ANODE 1
2. ANODE 2
3. ANODE 3
4. CATHODE 3
5. CATHODE 2
6. CATHODE 1

STYLE 16:
PIN 1. BASE 1
2. EMITTER 2
3. COLLECTOR 2
4. BASE 2
5. EMITTER 1
6. COLLECTOR 1

STYLE 17:
PIN 1. BASE 1
2. EMITTER 1
3. COLLECTOR 2
4. BASE 2
5. EMITTER 2
6. COLLECTOR 1

STYLE 18:
PIN 1. VIN1
2. VCC
3. VOUT2
4. VIN2
5. GND
6. VOUT1

STYLE 19:
PIN 1. I OUT
2. GND
3. GND
4. V CC
5. V EN
6. V REF

STYLE 20:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 21:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. N/C
6. CATHODE 1

STYLE 22:
PIN 1. D1 (i)
2. GND
3. D2 (i)
4. D2 (c)
5. VBUS
6. D1 (c)

STYLE 23:
PIN 1. Vn
2. CH1
3. Vp
4. N/C
5. CH2
6. N/C

STYLE 24:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 25:
PIN 1. BASE 1
2. CATHODE
3. COLLECTOR 2
4. BASE 2
5. EMITTER
6. COLLECTOR 1

STYLE 26:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 27:
PIN 1. BASE 2
2. BASE 1
3. COLLECTOR 1
4. EMITTER 1
5. EMITTER 2
6. COLLECTOR 2

STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 29:
PIN 1. ANODE
2. ANODE
3. COLLECTOR
4. EMITTER
5. BASE/ANODE
6. CATHODE

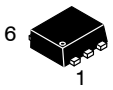
STYLE 30:
PIN 1. SOURCE 1
2. DRAIN 2
3. DRAIN 2
4. SOURCE 2
5. GATE 1
6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.




**onsemi** and ONSEMI. are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2019

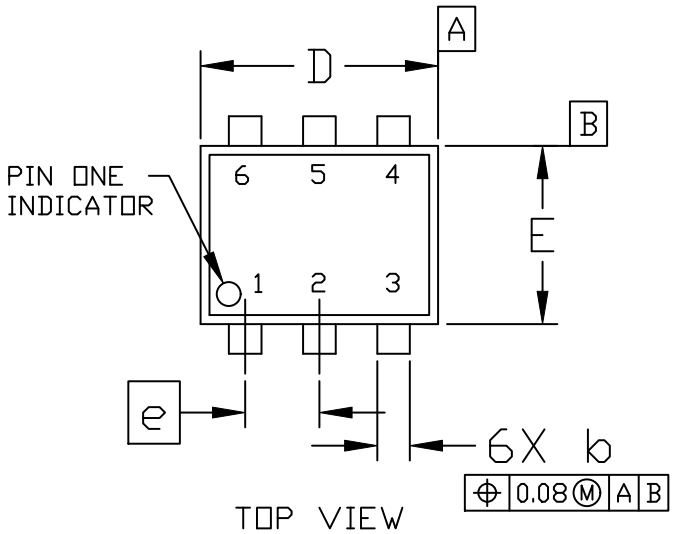



**SCALE 4:1**

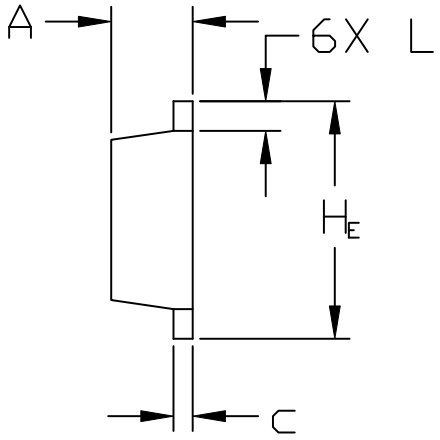
**SOT−563, 6 LEAD**
CASE 463A
ISSUE H

DATE 26 JAN 2021

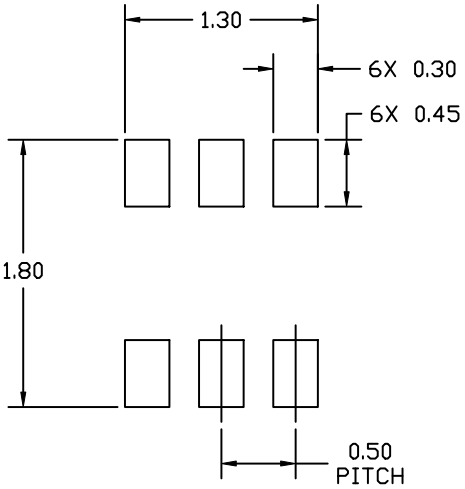
NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.




TOP VIEW




SIDE VIEW




RECOMMENDED MOUNTING FOOTPRINT*

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN. | NOM. | MAX. |
| A | 0.50 | 0.55 | 0.60 |
| b | 0.17 | 0.22 | 0.27 |
| c | 0.08 | 0.13 | 0.18 |
| D | 1.50 | 1.60 | 1.70 |
| E | 1.10 | 1.20 | 1.30 |
| e | 0.50 BSC | | |
| L | 0.10 | 0.20 | 0.30 |
| $H_E$ | 1.50 | 1.60 | 1.70 |



**onsemi** and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2019

**SOT−563, 6 LEAD**
CASE 463A
ISSUE H

DATE 26 JAN 2021

STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

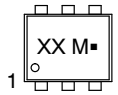
STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

**GENERIC**
**MARKING DIAGRAM***




XX = Specific Device Code
M = Month Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

| | | |
|---|---|---|
| **DOCUMENT NUMBER:** | **98AON11126D** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. |
| **DESCRIPTION:** | **SOT−563, 6 LEAD** | **PAGE 2 OF 2** |

**onsemi** and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

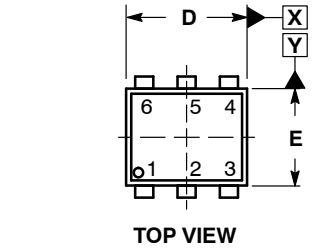
© Semiconductor Components Industries, LLC, 2019

# MECHANICAL CASE OUTLINE
## PACKAGE DIMENSIONS

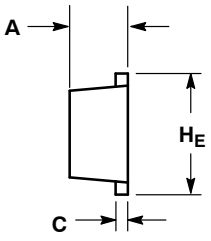
**SOT−963**
CASE 527AD
ISSUE E

**SCALE 4:1**

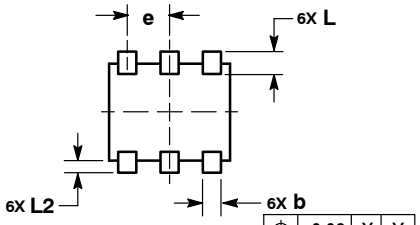
DATE 09 FEB 2010




**TOP VIEW**




**SIDE VIEW**

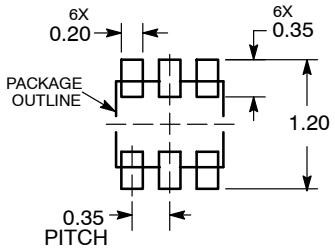



**BOTTOM VIEW**

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

| | MILLIMETERS | | |
|---|---|---|---|
| DIM | MIN | NOM | MAX |
| A | 0.34 | 0.37 | 0.40 |
| b | 0.10 | 0.15 | 0.20 |
| C | 0.07 | 0.12 | 0.17 |
| D | 0.95 | 1.00 | 1.05 |
| E | 0.75 | 0.80 | 0.85 |
| e | 0.35 BSC | | |
| $H_E$ | 0.95 | 1.00 | 1.05 |
| L | 0.19 REF | | |
| L2 | 0.05 | 0.10 | 0.15 |

### RECOMMENDED MOUNTING FOOTPRINT*




DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

STYLE 2:
PIN 1. EMITTER 1
2. EMITTER2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1

STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1

STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR

STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE

STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE

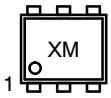
STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE

STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1

STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1

### GENERIC MARKING DIAGRAM*




X = Specific Device Code
M = Month Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

| | | |
|---|---|---|
| **DOCUMENT NUMBER:** | **98AON26456D** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. |
| **DESCRIPTION:** | **SOT−963, 1.00x1.00, 0.35P** | **PAGE 1 OF 1** |

**onsemi** and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2019